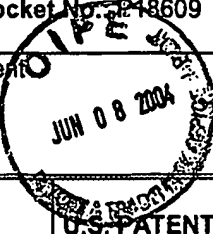


Form PTO-1449 (Modified)	Atty Docket No.: 218609	Serial No.: 10/828,958
List of Patents and Publications Statement (Use several sheets if necessary)		Applicant: Justin K. Brask et al.
		Filing Date: April 20, 2004

REFERENCE DESIGNATION						
U.S. PATENT DOCUMENTS						
Examiner Initials	Document No.	Class	Sub-Class	Filing date if appropriate		
CDW	AA	6,365,450 B1	Kim	438	216	
	AB					
	AC					
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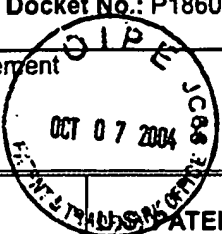
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	Document No.	Date	Country	Class	Sub-Class	Translation	
AP							
AQ							
AR							

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
	AS	
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	AW	
	AX	
	AY	
	AZ	

Examiner <u>Christian Wilson</u>	Date Considered <u>11/9/05</u>
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP-609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449 (Modified)		Atty Docket No.: P18609		Serial No.: 10/828,958	
List of Patents and Publications Statement (Use several sheets if necessary)				Applicant: Justin K. Brask et al.	
				Filing Date: April 20, 2004	



REFERENCE DESIGNATION			PATENT DOCUMENTS			
Examiner Initials	Document No.	Class	Sub-Class	Filing date if appropriate		
DW	AA	6,255,698 B1			Gardner et al.	
	AB	6,410,376 B1			Ng et al.	
DW	AC	6,586,288 B2			Kim et al.	
	AD	US 2002/0058374 A1			Kim et al.	
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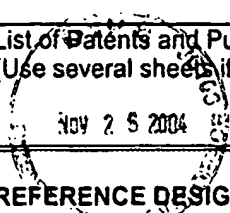
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	Document No.	Date	Country	Class	Sub-Class	Translation	
DW	AP	EP 0 899 784 AZ	3/3/1999	EP			
DW	AQ	GB 2 358 737 A	4/24/2001	UK			
	AR						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
DW	AS	Metz et al., "A Method for Making a Semiconductor Device Having a High-K Gate Dielectric Layer and a Metal Gate Electrode", Serial No. 10/839,077, Filed May 4, 2004
	AT	
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Examiner: <i>Christina Wilson</i>	Date Considered: <i>11/9/05</i>
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Form PTO-1449 (Modified)		Atty Docket No.: P18609		Serial No.: 10/828,958	
List of Patents and Publications Statement (Use several sheets if necessary)				Applicant: Justin K. Brask et al.	
				Filing Date: April 20, 2004	



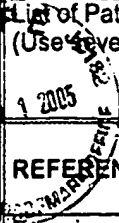
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cdw	AA	6,642,131 B2	Harada	438	591	
cdw	AB	6,667,246 B2	Mitsuhashi et al.	438	756	
cdw	AC	6,794,234 B2	Polishchuk et al.	438	199	
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FOREIGN PATENT DOCUMENTS							
No.		Document No.	Date	Country	Class	Sub-Class	Translation
	AQ						
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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
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Examiner <i>Christ Wilson</i>	Date Considered <i>11/9/05</i>
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Form PTO-1449 (Modified)		Atty Docket No.: P18609		Serial No.: 10/828,958	
List of Patents and Publications Statement (Use several sheets if necessary)				Applicant: Justin K. Brask et al.	
				Filing Date: April 20, 2004	
REFERENCE DESIGNATION			U.S. PATENT DOCUMENTS		
Examiner Initials		Document No.		Class	Sub- Class
	AA	6,727,130 B2	Kim et al.	438	199
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	AJ				
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	AL				
	AM				
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	AO				
	FOREIGN PATENT DOCUMENTS				
		Document No.	Date	Country	Class
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	AR				
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)					
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Examiner <i>Christina Wilson</i>			Date Considered <i>11/9/05</i>		
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Substitute for Form 1449/PTO <div style="display: flex; align-items: center; justify-content: center;"> <div> <h2 style="margin: 0;">INFORMATION DISCLOSURE</h2> <h3 style="margin: 0;">STATEMENT BY APPLICANT</h3> <p style="margin: 0; font-size: small;">(use as many sheets as necessary)</p> </div> </div>				Complete if Known	
		Application Number	10/828,958		
		Filing Date	April 20, 2004		
		First Named Inventor:	Justin K. Brask et al.		
		Art Unit	Unknown 2891		
		Examiner Name	Unknown Wilson		
		Attorney Docket Number	P18609		
U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
DW		US- 2001/0027005 A1	10/4/2001	Moriwaki et al.	
DW		US- 6,303,418 B1	10/16/2001	Cha et al.	
		US-			
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ² Number ⁴ Kind Code ³ (if known)				
DW		WO 01/97257 A	12/20/2001	Madhukar, Kucharita		
DW		EP 1 032 033 A	8/30/2000	Wilks, Glen D.		
DW		JP 2002-118175 A	4/19/2002	Toshiba Corp.		

Examiner Signature		Date Considered	11/1/05
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Form PTO-1449 (Modified)		Atty Docket No.: P18609		Serial No.: Unknown— <div style="text-align: right; font-size: 1.2em;">10823958</div>			
List of Patents and Publications Statement (Use several sheets if necessary)				Applicant: Justin K. Brask			
				Filing Date: April 20, 2004			
REFERENCE DESIGNATION			U.S. PATENT DOCUMENTS				
Examiner Initials		Document No.		Class	Sub-Class	Filing date if appropriate	
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	AB	6,184,072 B1	Kaushik et al.	438	197		
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	AD	6,475,874 B2	Xiang et al.	438	396		
	AE	6,514,828 B2	Ahn et al.	438	240		
	AF	6,544,906 B2	Rotondaro et al.	438	785		
	AG	6,617,209 B1	Chau et al.	438	240		
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	AI	6,620,713 B2	Arghavani et al.	438	585		
	AJ	6,689,675 B1	Parker et al.	438	585		
	AK	6,696,327 B1	Brask et al.	438	197		
	AL	6,696,345 B2	Chau et al.	438	387		
	AM	US2002/0197790 A1	Kizilyalli et al.	438	240		
	AN	US2003/0032303 A1	Yu et al.	438	770		
	AO	US2003/0045080 A1	Visokay et al.	438	591		
	FOREIGN PATENT DOCUMENTS						
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	AP						
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
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	AR	Doug Barlage et al., "High-Frequency Response of 100nm Integrated CMOS Transistors with High-K Gate Dielectrics", 2001 IEEE, 4 pages					
	AS	Lu et al., "Dual-Metal Gate Technology for Deep-Submicron CMOS Devices", dated April 29, 2003, 1 page					
	AT	Schwantes et al., "Performance Improvement of Metal Gate CMOS Technologies with Gigabit Feature Sizes", Technical University of Hamburg-Harburg, 5 pages					
	AU	Doczy et al., "Integrating N-type and P-type Metal Gate Transistors," Serial No. 10/327,293, Filed December 20, 2002					
	AV	Brask et al., "A Method for Making a Semiconductor Device Having a Metal Gate Electrode," Serial No. 10/704,497, Filed November 6, 2003					
	AW	Brask et al., "A Method for Etching a Thin Metal Layer," Serial No. 10/704,498, Filed November 6, 2003					
	AX	Brask et al., "A Method for Making a Semiconductor Device with a Metal Gate Electrode that is Formed on an Annealed High-K Gate Dielectric Layer," Serial No. 10/742,678, Filed 12/19/03					
	AY	Brask et al., "A Method for Making a Semiconductor Device that Includes a Metal Gate Electrode," Serial No. 10/739,173, filed December 18, 2003					
	AZ	Brask et al., "A CMOS Device With Metal and Silicide Gate Electrodes and a Method for Making It," Serial No. 10/748,559, filed December 29, 2003					
	BA	Doczy et al., "A Method for Making a Semiconductor Device that Includes a Metal Gate Electrode," Serial No. 10/748,545, filed December 29, 2003					
	BB	Shah et al., "A Method for Making a Semiconductor Device with a Metal Gate Electrode," Serial No. 10/809,880, filed March 22, 2004					
	BC	Shah et al., "A Replacement Gate Process for Making a Semiconductor Device that Includes a Metal Gate Electrode," Serial No. 10/809,853, filed March 24, 2004					
Examiner <div style="font-size: 1.2em;">Christian Wilson</div>		Date Considered <div style="font-size: 1.2em;">11/9/05</div>					
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